

IN THE CLAIMS

Please amend the claims as follows:

Claim 1 (Currently Amended): A plasma processing apparatus ~~(1)~~ for applying a plasma process to a process target ~~(W)~~, comprising:

a process chamber that applies ~~(2) for applying~~ a plasma process to said process target ~~(W)~~;

a mounting table ~~(16)~~, provided in said process chamber ~~(2)~~, for mounting that mounts thereon said process target ~~(W)~~;

a process gas supply unit that supplies ~~(4) for supplying~~ a process gas for applying the plasma process to said process target ~~(W)~~ into said process chamber ~~(2)~~;

a plasma generation unit that generates ~~(5, 7) for generating~~ plasma of the process gas supplied by said process gas supply unit ~~(4)~~ by applying a high-frequency voltage; and

a dike that confines ~~(18) for confining~~ the plasma gas generated by said plasma generation unit ~~(5, 7)~~ in an area above said process target ~~(W)~~ mounted on said mounting table ~~(16)~~,

wherein said dike ~~(18)~~, which serves as an opposite electrode for generating plasma gas, comprises includes:

a conductive member ~~(18a)~~ formed of a conductor~~[[,]]~~; and

a protruding portion formed to surround said mounting table and to be higher than a mounting surface of said mounting table,

wherein said conductive member ~~(18a)~~ is grounded, and wherein said protruding portion of said dike is formed to be higher than said process target mounted on said mounting table, so as to surround the area above said process target, and

wherein said plasma processing apparatus further comprises a lifting unit that lifts up or down said dike and said mounting table in said process chamber.

Claim 2 (Currently Amended): The plasma processing apparatus (1) according to claim 1,

wherein said dike (18) ~~comprises~~ includes an insulating member (18b) which covers said conductive member (18a) and electrically insulates between said conductive member (18a) and said mounting table (16).

Claim 3 (Canceled).

Claim 4 (Withdrawn-Currently Amended): The plasma processing apparatus (1) according to claim 1,

wherein an interval between a top end of said dike (18) and an inner wall of said process chamber (2) is 85 mm or smaller.

Claims 5-6 (Canceled).

Claim 7 (Withdrawn): A multi-chamber system, wherein said plasma processing apparatus according to claim 1 is provided in at least one chamber.

Claim 8 (New): The plasma processing apparatus according to claim 1,

wherein an interval between a top end of said protruding portion of the dike and an inner wall of said process chamber is 5 mm or smaller.

Claim 9 (New): The plasma processing apparatus according to claim 1,  
wherein an interval between a top end of said protruding portion of the dike and an  
inner wall of said process chamber is 2.5 mm or smaller.

Claim 10 (New): The plasma processing apparatus according to claim 8,  
wherein the interval between the top end of the protruding portion of the dike and the  
inner wall of the process chamber is configured to be set in accordance with a pressure in the  
process chamber.

Claim 11 (New): A plasma processing apparatus for applying a plasma process to a  
process target, comprising:

means for applying a plasma process to said process target;

means for supporting the process target thereon, the means for supporting being  
provided in said process chamber;

means for supplying a process gas for applying the plasma process to said process  
target into said process chamber;

means for generating plasma of the process gas by applying a high-frequency voltage;

means for confining the generated plasma gas in an area above said process target  
supported by the means for supporting, the means for confining including a conductive  
member and projecting higher than the process target so as to surround the area above said  
process target; and

means for lifting for lifting up or down the means for confining and said mounting  
table in said process chamber.